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AFOSR-TR. 86 - 0639

AD-A171 897

Project 764977/717636
Quarterly R & D Status Report

STRENGTH AND STRUCTURE OF $GA_{1-x}IN_x$ AS ALLOYS

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AIR FORCE OFFICE OF SCIENTIFIC RESEARCH (AFSC)

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Contract No. F49620-85-C-0129

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April 1986

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OSU

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1314 Kinnear Road
Columbus, Ohio 43212

86 9 15 121

REPORT DOCUMENTATION PAGE

1a. REPORT SECURITY CLASSIFICATION

unclass.

1b. RESTRICTIVE MARKINGS

2a. SECURITY CLASSIFICATION AUTHORITY

3. DISTRIBUTION/AVAILABILITY OF REPORT

2b. DECLASSIFICATION/DOWNGRADING SCHEDULE

Approved for public release,
distribution unlimited

4. PERFORMING ORGANIZATION REPORT NUMBER(S)

5. MONITORING ORGANIZATION REPORT NUMBER(S)

AFOSR-TR- 86-0639

6a. NAME OF PERFORMING ORGANIZATION

OHIO STATE UNIVERSITY

6b. OFFICE SYMBOL
(If applicable)

7a. NAME OF MONITORING ORGANIZATION

AFOSR

6c. ADDRESS (City, State and ZIP Code)

Research, Foundation
1314 Kinnear Road
Columbus OH 43212

7b. ADDRESS (City, State and ZIP Code)

Same as 8c

8a. NAME OF FUNDING/SPONSORING
ORGANIZATION

AFOSR/

8b. OFFICE SYMBOL
(If applicable)

NE

9. PROCUREMENT INSTRUMENT IDENTIFICATION NUMBER

F49620-85-C-0129

8c. ADDRESS (City, State and ZIP Code)

Bolling AFB DC 20332-6448

10. SOURCE OF FUNDING NOS.

PROGRAM
ELEMENT NO.

6102F

PROJECT
NO.3526
DARPATASK
NO.

10

WORK UNIT
NO.

11. TITLE (Include Security Classification)

STRENGTH AND STRUCTURE OF Gal-xInxAs ALLOYS

12. PERSONAL AUTHOR(S)

Faber and Hirth

13a. TYPE OF REPORT

QUARTERLY (second)

13b. TIME COVERED

FROM 01 Jan 86 to 31 Mar 86

14. DATE OF REPORT (Yr., Mo., Day)

15. PAGE COUNT

16. SUPPLEMENTARY NOTATION

17. COSATI CODES

FIELD

GROUP

SUB. GR.

18. SUBJECT TERMS (Continue on reverse if necessary and identify by block number)

19. ABSTRACT (Continue on reverse if necessary and identify by block number)

20. DISTRIBUTION/AVAILABILITY OF ABSTRACT

UNCLASSIFIED/UNLIMITED ☐ SAME AS RPT. ☐ DTIC USERS ☐

21. ABSTRACT SECURITY CLASSIFICATION

22a. NAME OF RESPONSIBLE INDIVIDUAL

KEVIN J. MALLOY, Capt., USAF

22b. TELEPHONE NUMBER
(Include Area Code)

202-767-4932

22c. OFFICE SYMBOL

AFOSR/NE

Strength and Structure of $\text{Ga}_{1-x}\text{In}_x\text{As}$ Alloys

Quarterly R & D Status Report

April 15, 1986

APRA Order 5526

Program Code 5Y10

Contractor: Air Force Office of Scientific Research

Contract Dates: September 1, 1985 - August 31, 1986

Contract Amount: \$142,286

Contract Number: F49620-85-C-0129

Co-Principal Investigators:
Katherine T. Faber and John P. Hirth
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Accession For	
NTIS GRA&I	<input checked="checked" type="checkbox"/>
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Unannounced	<input type="checkbox"/>
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↙ The strengthening effect of GaAs by indium additions is under examination. Solid solution strengthening by $\text{InAs}_4^{1/4}$ solute units has been predicted and is studied via mechanical measurements complemented by electron microscopy. In this second quarterly report, hardness measurements for three $\text{Ga}_{1-x}\text{In}_x\text{As}$ compositions from R. T. to 900 C are complete and the second stage of the experimental work, compression testing as a function of temperature and strain rate, is underway. X

(1) Progress

Vickers hardness measurements on (100) GaAs, $\text{Ga}_{0.9975}\text{In}_{0.0025}\text{As}$ and $\text{Ga}_{0.99}\text{In}_{0.01}\text{As}$ wafers (obtained from Westinghouse R&D Center) were made over the temperature range of room temperature to 900 C. Silox-coated $\text{Ga}_{0.99}\text{In}_{0.01}\text{As}$ wafers, also from Westinghouse, were examined so that hardness tests could be extended to higher temperatures. These attempts were unsuccessful, because (a) surface coatings were pitted and (b) the coating stuck to the indenter so that no indentations could be made. A modified hardness test with a small enclosure around the specimens to minimize the loss of arsenic is being examined.

An appreciable difference in hardness between undoped and In-doped GaAs is seen only above 300 C, with $\text{Ga}_{0.99}\text{In}_{0.01}\text{As}$ being 40% harder than the undoped crystal at 900 C. The hardness measurements described here show similar trends as the lower yield point measurements by Tabache and Haller at University of California, Berkeley on In-doped and undoped single crystals.

Consistent with the solid solution strengthening model, greater amounts of indium result in higher hardnesses. By virtue of their higher hardness, the alloys containing indium could be inferred to have a higher plateau stress levels. Since hardness is linearly related to the yield strength and critical resolved shear stress (CRRS), the relative

enhancement in CRSS is expected to be of the same magnitude as the hardness increase. Extrapolation of the hardness data to the melting point of GaAs, though not justifiable because of the change in flow mechanism at higher temperatures from pure glide control to climb-controlled glide, would yield hardness values, and consequently CRRS values which cannot fully explain the strengthening effect of indium. Unconfirmed calculations of the thermal stress experienced by the crystal during growth suggest that a much larger strengthening effect must be present to explain the significant reduction in dislocation density.

Compression testing at strain rates more comparable to crystal growth conditions will be started in the upcoming quarter and should provide further information concerning the deformation-controlling processes. Two (100) seed crystals of undoped and In-doped GaAs were received from Westinghouse and tests will be done with [100] as the compression axis.

(2) Special equipment constructed

A compression fixture for operation at temperatures to 1200 C is under construction. The ceramic compression rams, specimen positioning and alignment fixtures were ordered and received. An existing furnace and retort will be used to surround the compression fixture. The sample will be positioned in a B_2O_3 "bath" to prevent the loss of As.

(3) Change in key personnel

None.

(4) Substantive information derived from meetings

An informal meeting with the Devices Group of the Westinghouse Research and Development Center in Pittsburgh was arranged on March 20, 1986 to exchange views and information. Drs. R. Noel Thomas, Shaun

McQuiggan and Don Hobgood from Westinghouse and Profs. J. P. Hirth and K. T. Faber and Dr. S. Guruswamy from Ohio State were the main participants. Discussion topics included compression testing work at Westinghouse on undoped and In-doped GaAs up to 600 C, the general deformation behavior of III-V compounds with particular emphasis on the very high temperature region, and the possibility of increased strength at higher temperature due to solute drag. The current results of high temperature hardness and toughness were discussed in the light of thermal stress calculations of the crystal growth process.

Arrangements were made at this meeting for Westinghouse to supply additional GaAs samples for compression testing. Some II-VI compounds will also be made available for fracture toughness testing, resulting from discussions of concerns in the growth of II-VI compounds.

(5) Problems of concern

None.

(6) Fiscal status

- (a) Amount currently provided for contract: \$110,000
- (b) Expenditures and commitments to 3/31/86: \$ 58,863.15
March financial statement is attached
- (c) Amount needed to complete work: \$51,136.85
- (d) Estimated date of completion: 8/31/86

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RET10 RETF10C PROJECT FINANCIAL SUMMARY SYS DATE 4/16/86 TIME 14:37:51
 OPTION: 01 KEY: 717436 PROJ 717436 MFN 764977 MONTHLY DATA AS CF: 3/31/86
 PI KATHERINE T FABER DEPT AF OFC SCI RES SD 9/01/83
 COPI JOHN P HIRTH 1420 F49620-85-C-0129 ED 6/31/86
 WKSTN 4 RPN 060006 DO WOODY PA VENTRESCA IDC B 44 45.00
 DESCRIPTION BUDGET EXP MONTH EXP TO DTE COMMITMENTS UNEN BAL
 SPONSOR
 S & W -REL 10190.00 1269.52 4108.56 3472.60 608.64
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OPTION: 07 KEY: 717636

MONTHLY DATA AS OF: 3/31/86

PRINCIPAL INVESTIGATOR NAME: KATHERINE T FABER

ADM NAME VENTRESCA

CO-PRINCIPAL INVESTIGATOR NAME: JOHN P HIRTH

DO NAME WOODY

OUTSTANDING COMMITMENTS

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CODE	NUMBER	LTR	DATE	NUMBER	FIRST NAME	AMOUNT	AMOUNT
102	288263	I	6/30/86	288263	SIVARARMAN GURUSWAMY		6480.00
112	288263	I	6/30/86	288263	SIVARARMAN GURUSWAMY		388.41
130	223665	J	6/15/86	223665	KATHERINE THERESA FABER		2875.00
140	223665	J	6/15/86	223665	KATHERINE THERESA FABER		402.50
132	907660	A	8/31/86	907660	LAUREN RAE WERLING		597.60
142	907660	A	8/31/86	907660	LAUREN RAE WERLING		81.94
					TOTAL PERSONNEL SERVICES		11325.45
316	086579		3/27/86		L.H. MARSHALL COMPANY		30.75
316	477850		3/18/86		KISTLER INSTRUMENT CORP.		1578.43
					TOTAL MATERIAL & SERVICE		1609.18
718	209105		3/20/86		JOHN P HIRTH		150.00
718	209255		3/20/86		KATHERINE T FABER		123.00
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OPTION: 07 KEY: 717636 MONTHLY DATA AS OF: 3/31/86
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COST PO-TA APPT PO-TA VEN/EMP VENDOR/EMPLOYEE C/S COMMIT SPON COMMIT
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112	288263	90	H60001		FEB 86 INS CHRG 81082387		22.18
112	288263	90	I60001		MAR 01-31,86-MON-RETIREN		296.14
130	223665	90	I60001		MAR 01-31,86-REL-BASE SA		1150.00
132	907660	90	I60001		MAR 01-31,86-REL-BASE SA		119.52
140	223665	90	I60001		MAR 01-31,86-REL-INS ACC		40.07
140	223665	90	I60001		MAR 01-31,86-REL-RETIREN		161.00
142	907660	90	I60001		MAR 01-31,86-REL-INS ACC		13.94
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					TOTAL PERSONNEL SERVICES		3983.16
316		90	I60011		STORES CHARGES - MAR 86		34.13
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OPTION: 11 KEY: 210 717636

SYSTEM DATE: 4/16/86 TIME: 14:39:16

MONTHLY DATA AS OF: 3/31/86

OSURF TRANSACTIONS DISTRIBUTION SUMMARY

GENERAL LEDGER #: 210				SUBSIDIARY ACCOUNT NO: 717636			
COST	OPEN	TRN	SOURCE	CAN	TRANSACTION	COST EXP	SPONS EXP
CODE	ITEM	CDE	REF	NUMBER	DESCRIPTION	AMOUNT	AMOUNT
					TOTAL MATERIAL & SERVICE		1383.80
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					TOTAL INDIRECT COST		2415.13
					TOTAL FOR PROJECT		7782.09

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ROLLUP
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HIGH TEMPERATURE HARDNESS OF $\text{Ga}_{1-x}\text{In}_x\text{As}$

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ABSTRACT

Substantial solid solution strengthening of GaAs by In acting as InAs_4 units has recently been predicted for an intermediate temperature, plateau region. This strengthening could account, in part, for the reduction of dislocation density in GaAs single crystals grown from the melt. Hardness measurements at high temperatures up to 900 °C, have been carried out on (100) GaAs, $\text{Ga}_{0.9975}\text{In}_{0.0025}\text{As}$ and $\text{Ga}_{0.99}\text{In}_{0.01}\text{As}$ wafers, all of which contain small amounts of boron. Results show a significant strengthening effect in In-doped GaAs. A nominally temperature-independent flow stress region is observed for all three alloys. The In-doped GaAs shows a higher plateau stress level with increasing In content. The results are consistent with the solid solution strengthening model. The magnitude of the solid solution hardening is sufficient to explain the reduction in dislocation density with In addition.

INTRODUCTION

Doping of GaAs with In in single crystals grown by the Czochralski process has been known to reduce the dislocation density from $10^3 - 10^4$ cm/cc to $< 10^2$ cm/cc.¹ There is a consensus that the generation of dislocations in GaAs and other III-V compounds occurs when the thermal stress imposed on the crystal during growth exceeds the critical resolved shear stress (CRSS) of the crystal. While the minimization of thermal gradients, and hence, the stresses during growth are achieved by the control of process parameters such as B_2O_3 encapsulant height, cone angle, diameter control and ambient pressure, enhancing the inherent strength (CRSS) of the crystal is achieved by addition of isovalent dopants as well as other Group IV and VI elements. Of these, the isovalent In and the Group IV element Si have been found to be the most effective.² However In doping is desirable because of the minimal influence on the electrical behavior of the GaAs. The mechanism of dislocation density reduction at such low concentration levels of the dopant is yet to be resolved unequivocally. The drastic reduction in dislocation density suggests a very large increase in the strength with In doping. Thermal stress calculations suggest that the maximum stress experienced by the crystal is several times that of the extrapolated CRSS of an undoped GaAs crystal.³ It has been suggested⁴ that hardening akin to solid solution hardening occurs in GaInAs with an $InAs_4$ tetrahedral cluster being the solute unit that causes strengthening. EXAFS studies by Mikelson and Boyce⁵ show that in the Ga-In-As system, the overall lattice parameter varies linearly with In concentration in accordance with Vegard's law, while the Ga-As and In-As bond lengths are

essentially the same as in the corresponding pure crystals. The interpretation of these results⁴ is that each In atom together with its four nearest As neighbors acts as a center of strain analogous to a solute atom in a metal. Such a unit would cause a local tetrahedral strain field corresponding to a volume dilatation, $\delta V/V$, of about 21%. This large strain field should result in substantial solid solution strengthening in an intermediate temperature, plateau region. When the dislocations are pinned strongly by these strain centers, the increase in strength for an alloy containing 5×10^{19} atoms/cc of In is estimated to be about 120 %.

Generally compounds such as GaAs have strong temperature dependences for flow at low temperatures, corresponding to a rate controlling mechanism related to the intrinsic lattice resistance or Peierls' barrier. An athermal, plateau region appears at intermediate temperatures corresponding to extrinsic effects such as solid solution hardening, while at high temperatures other creep-type mechanisms would be applicable. The low temperature process consists of dislocation motion controlled by nucleation and lateral propagation of double kinks. With an increase in temperature, the nucleation and motion of double kinks occurs much more easily and the flow stress drops sharply (Figure 1). Misfit strain centers promote double kink nucleation while impeding the subsequent lateral propagation of the two kink segments.⁶ The solute addition at low concentration levels could result in either hardening or softening depending on the magnitude of these opposing effects. However, the softening effect should be most prominent at the lowest temperatures where the double kink model is dominant and should

be less pronounced as the extrinsic athermal region is approached. Hence, a transition from softening to hardening with increasing temperature below the plateau region would be expected, analogous to observations for b.c.c. metals where the Peierls' mechanism is operative at low temperatures.⁷

In the athermal region beginning at about 700 °C for GaAs, double-kink nucleation no longer controls dislocation motion. In this region, the resistance to dislocation glide derives mainly from the interaction with solutes, and other defects such as intersecting dislocations and the dislocation motion occurs by breaking away from these pins. As in the case of solution strengthened metals,⁸ a nominally temperature independent flow stress region would be observed. In actuality, the flow stress is not truly independent in the plateau region but the slope of the flow stress-temperature plot is significantly less in this region than at lower temperatures.⁸ In this plateau region, the thermal component of flow stress is significantly less than the athermal component. The temperature-independent flow stress level (plateau-stress) would increase with increasing solute content. This region is expected to extend to a significant fraction of the melting temperature. Beyond this temperature, the flow stress would be determined by diffusion-controlled deformation processes.

This work concerns the experimental measurement of the flow stress and hardness as a function of temperature and In content. High temperature hardness testing is used to estimate the influence of indium on CRSS and yield strength and to confirm the existence of the plateau-stress. The yield stress level is approximately 1/3 of the hardness

value⁹ so the latter indicates expected trends for yield stress.

EXPERIMENTAL WORK

The hardness tester used in this study was designed and fabricated specifically for the testing of GaAs. Loading is applied by dead weights with a counterbalance arrangement to vary the load from 0.1 N to 3 N. The indenter is raised and lowered at a constant rate of 3 mm/minute by a screw mechanism. The furnace used is a low heat capacity Pt-20%Rh resistance wire-wound unit capable of rapid heating and cooling rates and a maximum temperature of 1500 °C. Ultra high purity argon, flowing into the enclosure, is used to cool the upper part of the indenter shaft. Hardness measurements were made from room temperature to 900 °C with a Vickers diamond pyramid indenter.

Testing was performed on (100) surfaces of wafers grown by the LEC method at Westinghouse Research and Development Center. Three compositions, undoped GaAs, $\text{Ga}_{0.9975}\text{In}_{0.0025}\text{As}$ and $\text{Ga}_{0.99}\text{In}_{0.01}\text{As}$, all semi-insulating, were studied. The concentration of In atoms in the above three alloys were 0, 5.5×10^{19} and 2.2×10^{20} atoms/cc. The indium content was confirmed by atomic absorption spectroscopy. All three alloys also contained boron at levels of 2×10^{18} atoms/cc. Boron contents were determined by Spark Source Mass Spectroscopy analysis at the Battelle Columbus Laboratories. All hardness data are normalized by the shear modulus to give the residual temperature dependence related to the mechanisms. Data for the Voight average shear modulus were calculated from the anisotropic elastic constants given as a function of temperature by Jordan.¹⁰

RESULTS AND DISCUSSION

Figure 2 shows the hardness test results for GaAs, $\text{Ga}_{0.9975}\text{In}_{0.0025}\text{As}$ and $\text{Ga}_{0.99}\text{In}_{0.01}\text{As}$ (100) wafers. All data points represent the average of 10 hardness readings. The standard deviation for the sets of data are also shown for the high temperature region (Fig. 2b). Table 1 also summarizes the hardness values for these three alloys. As indicated in figure, the hardening effect is significant relative to the scatter. A significant difference in hardness between undoped and In-doped GaAs is seen only above 300 °C. The hardness drops sharply with temperature and flattens out at higher temperatures indicative of the existence of the plateau stress region. The shape of the curve is very similar to that observed for metals exhibiting plateau behavior.⁸ By virtue of their higher hardness, the alloys containing In are inferred to have a higher plateau stress level. The increase in hardness compared to the undoped material is about 40% at 900 °C for the highly In doped alloy. Both the In-associated effects of the softening-hardening transition at low temperatures and the presence of the plateau region are consistent with the model discussed previously of Peierls' control superseded by solid solution hardening. The interpretation of the solid solution hardening effect in terms of pinning would require the dislocation configuration to be of a smoothly bowed, line-tension type. This is in accordance with the transmission electron microscope observations of Laister and Jenkins,¹¹ who found bowed arrays for undoped GaAs after deformation at 800 °C. The plateau behavior for undoped GaAs in Fig. 2 would then be associated with pinning caused by dislocation intersections, residual impurities, jogs, or antisite

defects. Alternatively, another solid solution hardening effect could be applicable. If dislocation motion occurred by double kink nucleation and growth, solute hardening would be manifested through a retardation of the growth step of lateral kink propagation, with the kink pinning effect still being proportional to δV . The similar plateau behavior for GaAs with and without In would then be a logical consequence since the same detailed mechanism of dislocation motion would be appropriate for both cases. Deformation of GaAs at the low temperatures of 320 °C and 400 °C does give straight dislocations^{12,13} consistent with a double kink model and the interpretation of the first stage of deformation in Fig. 1. We plan to undertake transmission electron microscope studies of the deformed alloys to determine whether the plateau region specimens correspond to bowed or straight dislocations to decide which of the above models is applicable. In the context of the present work, however, either model corresponds to a solid solution hardening effect of In.

Hardness is approximately equal to three times the lower yield stress.⁹ Moreover, the critical resolved shear stress (CRSS) equals the yield stress times the Schmid factor of about 0.5.¹⁴ Thus, the CRSS is approximately equal to $H/6$. The CRSS obtained from hardness data is presented as a function of temperature in Figure 3. For comparison, also shown are CRSS data from compression tests on undoped Bridgman crystals by Swaminathan and Copely¹⁵ and on undoped and In-doped LEC crystals by Tabache,¹⁶ both of which also represent values for the lower yield stress. The greater strength of the present crystals with no In doping may be associated with the presence of boron. Boron, an isoelectronic substitution for gallium, would produce a larger size mismatch, $\delta V/V$

=50%, than In, but an attendant lower solubility. Hence, it should also be a strong hardener if uniformly distributed in solution, an effect verified experimentally,¹ but could lead to internal stresses and dislocation generation if present in an inhomogeneous distribution or as precipitates.

Extrapolation of data from the present work, for the undoped and highly doped cases, to the melting point T_m gives CRSS values of 15 and 23 MPa respectively. The maximum resolved shear stresses predicted by theory^{3,17,18} to arise from thermal stresses at temperatures near T_m during crystal growth is 20 MPa. Thus, the present results suggest that crystals highly doped with In and containing B, have sufficient solid solution hardening to prevent yielding and accompanying dislocation generation during crystal growth. Further work is needed to resolve the difference between the present results and the compression test results in Fig. 3, in particular with respect to the possible role of boron.

While the above results would suffice to explain the suppression of dislocation formation by means of In additions, the extrapolation of the plateau data to the melting point is questionable, because there is most likely an intervening change in the deformation mechanism. Since GaAs has a structure similar to Si and the deformation map for GaAs is not available at the present time, the Si deformation map¹⁹ is used here as a guideline for this possible transition in mechanism. Figure 4 presents data extracted from the Si map for strain rates of 10^{-3} to 10^{-7} s⁻¹. The flow behavior undergoes a transition from flow following the double kink model to that of a power law creep model at about $0.5T_m$. For GaAs, the intervention of solid solution hardening is expected to move

the transition to power law creep to higher homologous temperatures, but, on the basis of all available deformation map data¹⁹ to still leave a region of power law creep below the melting point. The cellular dislocation networks present in as-grown GaAs crystals with dislocation densities of the order of 10^3 - 10^4 cm/cc provide indirect evidence that climb processes are involved in the deformation occurring during crystal growth. As indicated in Fig. 4, the transition to power law creep at a given strain rate and temperature is less than that for double-kink flow extrapolated to the same conditions. However, even for the power law creep region, \ln can have a hardening influence.

In the region of power law creep, the dislocation velocity, and hence, the flow stress level would depend on the lattice interdiffusion coefficient or diffusivity. In this regime, the dislocation velocity for a given applied stress is given by¹⁹

$$v = \frac{D_v \sigma_n \Omega}{b k T}$$

Here D_v is the bulk diffusivity, σ_n is the local normal stress that produces a climb force on the dislocation, k is Boltzmann's constant and Ω is the atomic volume. Because σ_n is proportional to the flow stress σ_s and the average dislocation velocity is proportional to the strain rate $\dot{\epsilon}$, the latter is given by¹⁹

$$\dot{\epsilon} = \frac{A D_v \mu b}{k T} \left[\frac{\sigma_s}{\mu} \right]^3$$

where μ is the shear modulus, A is a dimensionless constant, and b is the length of the Burgers vector. For a binary compound, D_v is replaced by $D_{eff} = D_{Ga} D_{As} / (D_{Ga} + D_{As})$.¹⁹ Thus, the stress for a given strain rate would be controlled in the GaAs lattice by the slower of

the diffusing species which is arsenic. The influence of solute elements on the diffusion in the arsenic sublattice would thus be an important factor in determining the effect of solute elements on the deformation behavior. The trapping of arsenic vacancies because of elastic interactions or electronic interactions with In solute centers would be a possible factor that could reduce D_{eff} , and hence, provide a hardening effect in the power law creep regime.

At high temperatures, where solute atoms are mobile, resistance to dislocation motion also comes from the drag of a solute atmosphere by the dislocation. The force-velocity relationship for this Cottrell drag has been treated in detail.²⁰ For a given dislocation velocity v , the drag stress increment caused by the solute atmosphere varies as the square of the strength of solute-dislocation interaction δV and inversely as the effective diffusivity. The solute drag stress versus temperature curve would exhibit a maximum and if present, would be superposed on the strength versus temperature plot in Fig. 1. Because of very low diffusivities in the GaAs lattice, the solute drag effect is expected at quite high temperatures. A possible effect of this type is shown by the dotted line in Figure 1.

All of the preceding discussion has been in terms of quasi-steady state flow corresponding to deformation at and subsequent to the lower yield point. An additional hardening-type influence of In could be manifested if the deformation during crystal growth occurred mainly in the transition region reflected by the microyield stress, the upper yield point and deformation between the upper and the lower yield points. A retarding effect of In on dislocation motion during

multiplication would tend both to increase the upper yield point and to prolong the strain range between the upper and lower yield points.^{21,22} The microyield stress, at which dislocation motion begins, would also be increased by such a retarding effect.

Thus while the plateau stress data extrapolated from 900°C indicates sufficient hardening to suppress flow on the basis of estimated thermal stresses, other hardening or softening effects associated with different deformation mechanisms above 900°C could be present. Such mechanisms are expected on the basis of theory. We are presently extending the deformation work to temperatures above 900 °C where conventional indentation methods are inapplicable.

SUMMARY

High temperature hardness tests at up to 900 °C of undoped and In-doped GaAs showed an appreciable strengthening effect of In in GaAs. The existence of an athermal, plateau stress region is indicated for the three alloys. The GaAs containing In shows a higher plateau stress level compared to GaAs with no In. Calculations suggest that the hardening produced by indium is sufficient to exceed the thermal stress experienced by the crystal during growth. However studies, at higher temperatures are needed to resolve the possibility of a change in the deformation mechanism near the melting point. Strengthening at higher temperatures with In additions is consistent with a solution hardening model for dislocation density reduction in In-doped GaAs.

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ACKNOWLEDGEMENTS

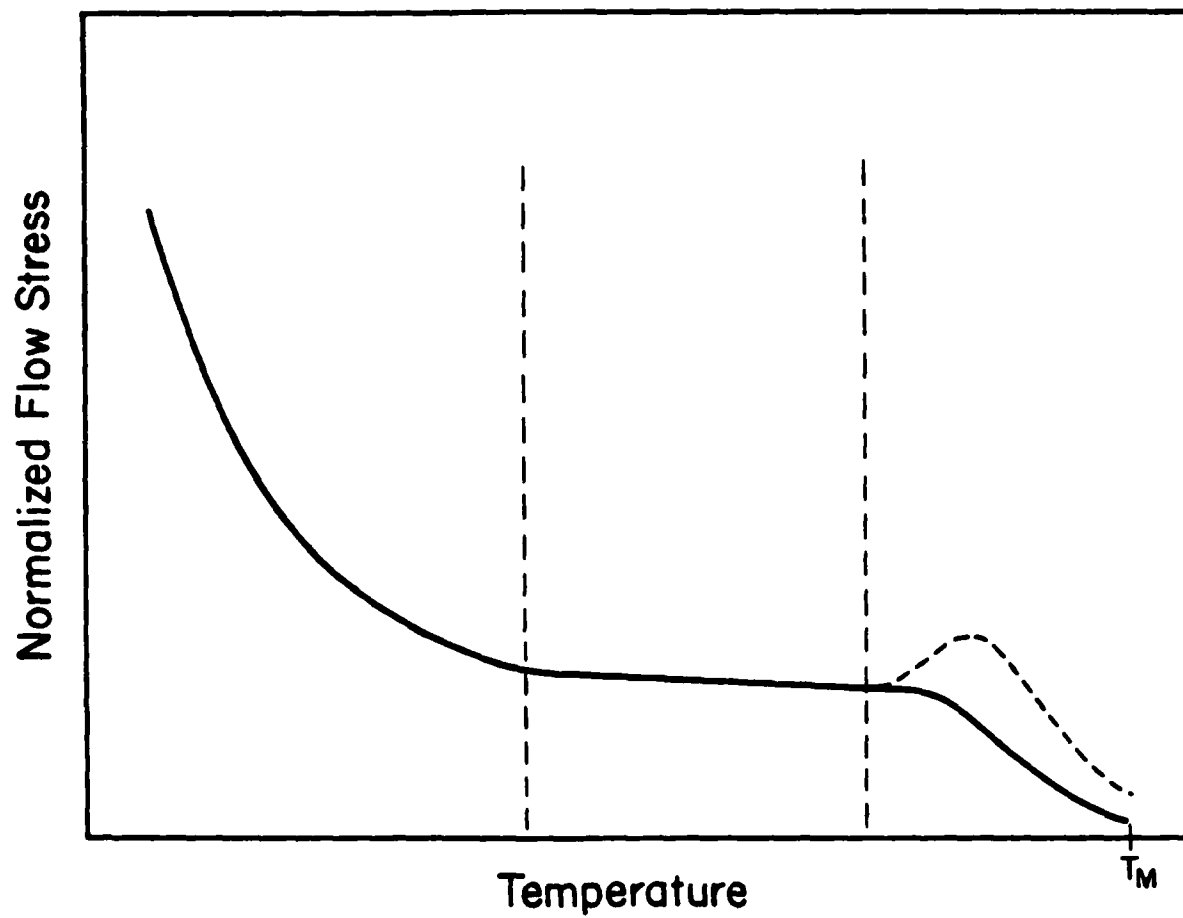
The authors are grateful for the support of this work by the Defence Advanced Research Projects Agency (DOD), DARPA Order No. 5526, monitored by AFOSR under Contract # F49620-85-C-0129, and for the help of R.N. Thomas and other members of the Devices Group, at the Westinghouse R&D Center, for providing materials for this research under their contract with DARPA # DARPA-Westinghouse-N-00014-84-C-0632 as well as for contributing helpful discussions.

Table I. Hardness data for all three alloys as a function of temperature.

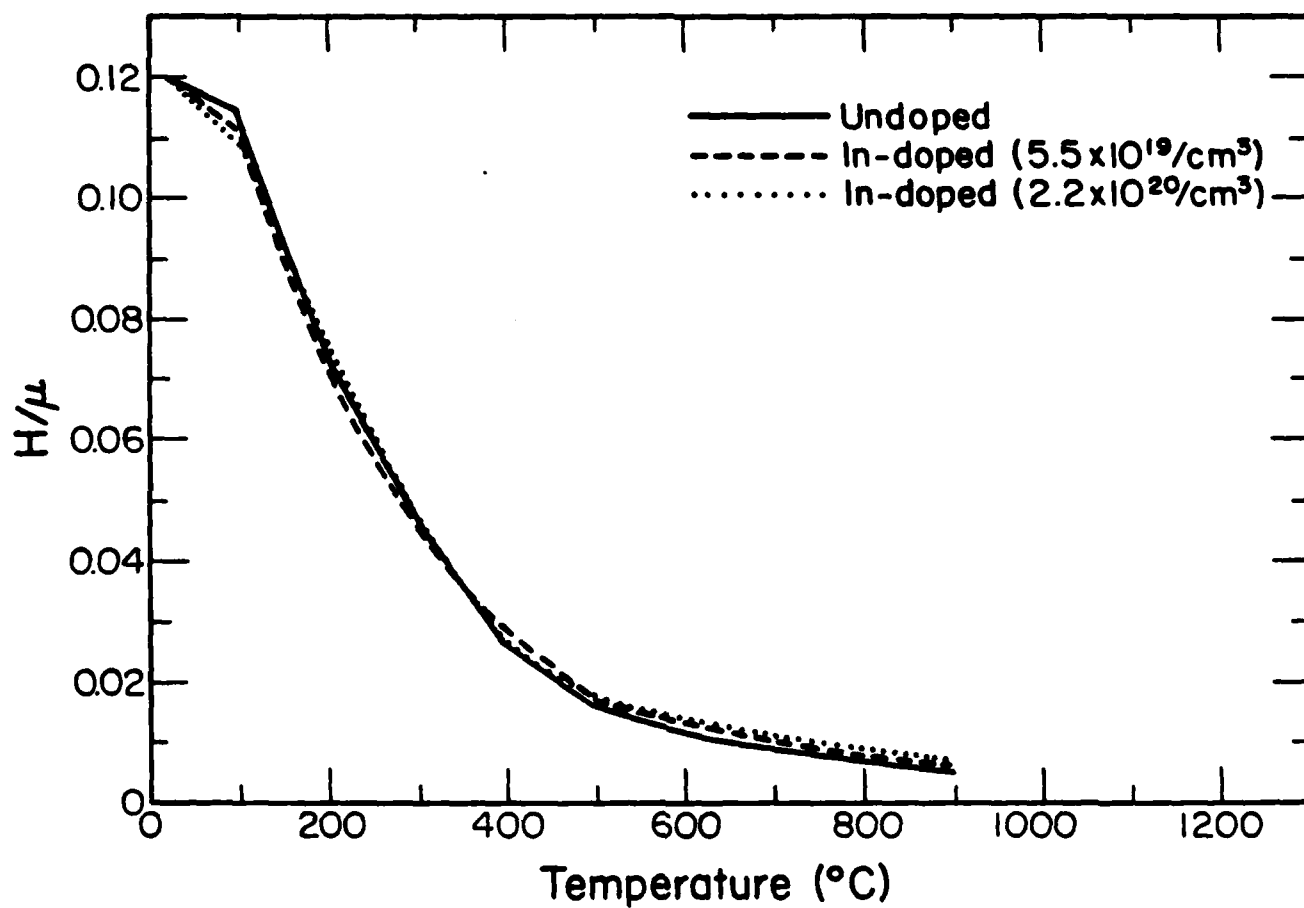
TEMPERATURE C	HARDNESS (GPa)		
	GaAs	Ga _{0.9975} In _{0.0025} As	Ga _{0.99} In _{0.01} As
25	5.82 ±0.2	5.82 ±0.2	5.92 ±0.22
100	5.52 ±0.16	5.39 ±0.15	5.26 ±0.2
200	3.50 ±0.3	3.41 ±0.21	3.65 ±0.1
300	2.23 ±0.15	2.13 ±0.18	2.14 ±0.25
400	1.20 ±0.03	1.33 ±0.04	1.19 ±0.06
500	0.72 ±0.02	0.76 ±0.04	0.79 ±0.01
600	0.52 ±0.03	0.58 ±0.014	0.64 ±0.013
700	0.38 ±0.014	0.45 ±0.015	0.49 ±0.03
800	0.291±0.01	0.324±0.01	0.38 ±0.01
900	0.21 ±0.01	0.26 ±0.01	0.293±0.01

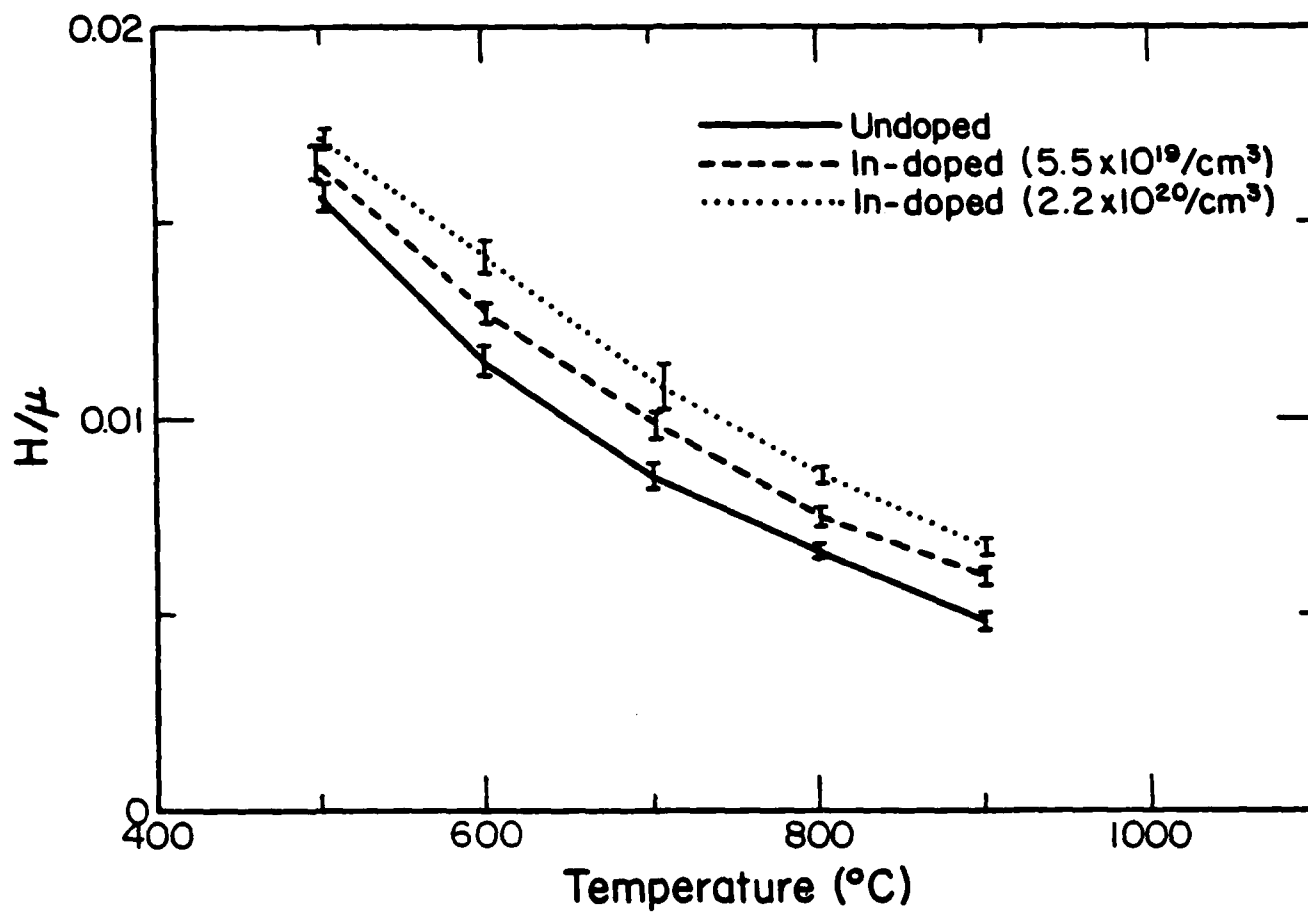
Figure Captions

1. Schematic normalised flow stress versus temperature curve for GaAs at a constant strain rate.
2. Normalised hardness versus temperature plot for GaAs, $\text{Ga}_{.9975}\text{In}_{.0025}\text{As}$ and $\text{Ga}_{.99}\text{In}_{.01}\text{As}$.
3. Critical resolved shear stress estimated from hardness data compared with the compression test data of Swaminathan and Copely¹⁵ on undoped GaAs and of Tabache¹⁶ on undoped and In-doped LEC GaAs.
4. A section of deformation mechanism map of Si which belongs to the same iso-mechanical group as GaAs.¹⁹



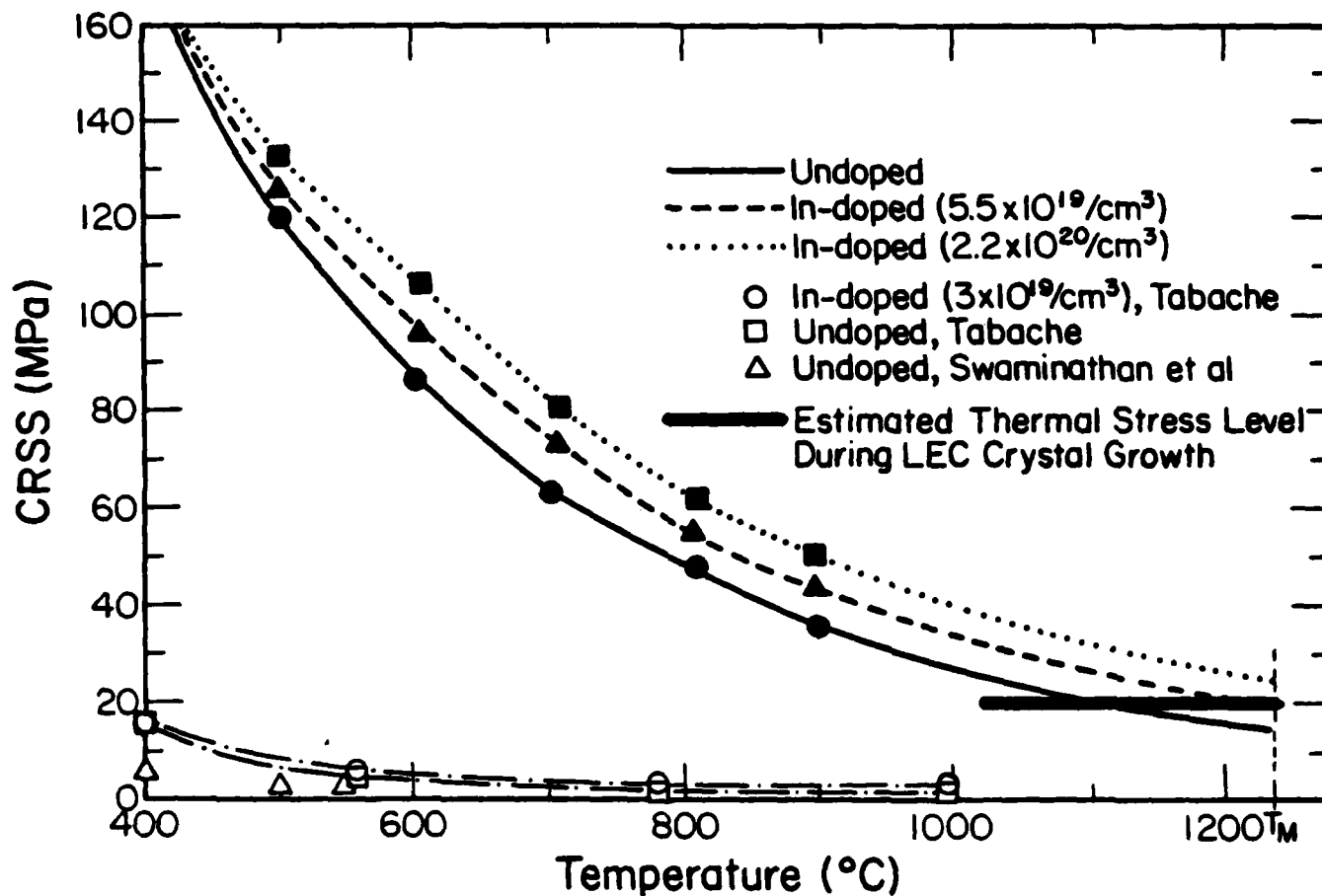
1. Schematic normalised flow stress versus temperature curve for GaAs at a constant strain rate.



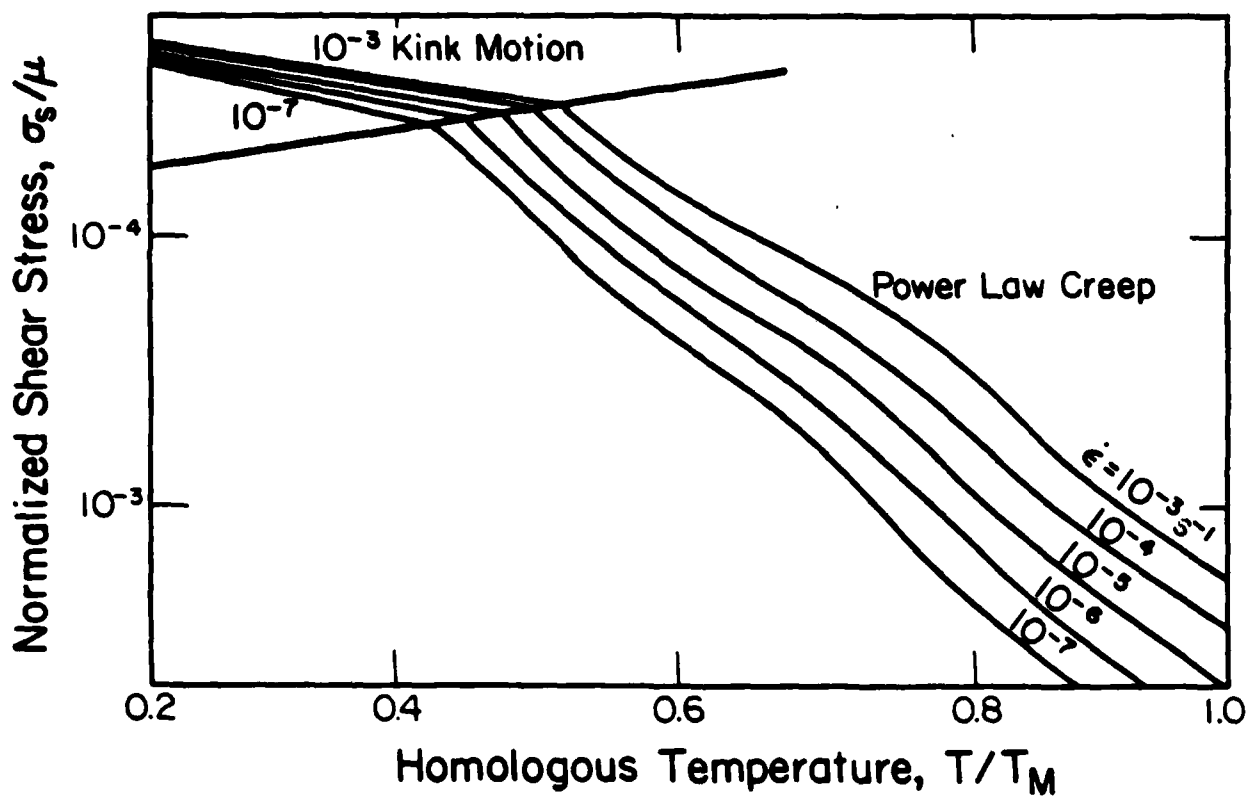


2b

2. Normalised hardness versus temperature plot for GaAs, $\text{Ga}_{0.9975}\text{In}_{0.0025}\text{As}$ and $\text{Ga}_{0.99}\text{In}_{0.01}\text{As}$.



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Figure 4.